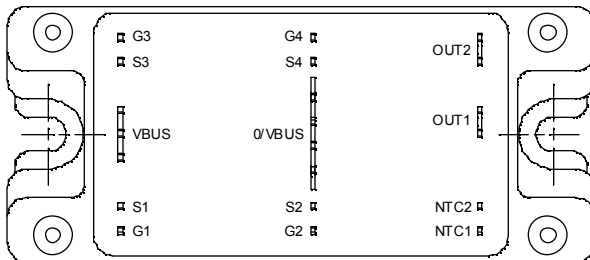
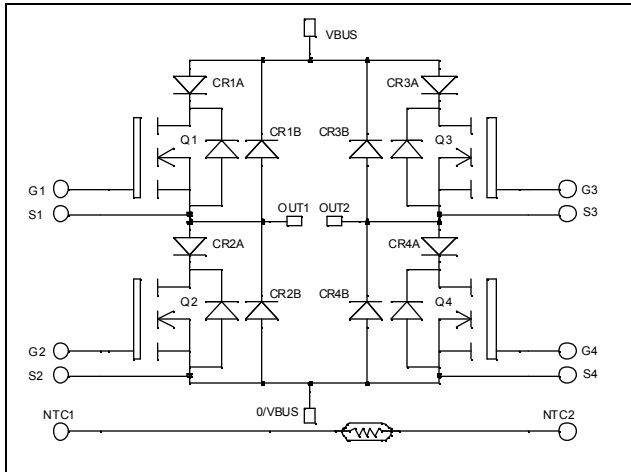


Full bridge Series & parallel diodes MOSFET Power Module

$$V_{DSS} = 200V$$

$$R_{DSon} = 20m\Omega \text{ typ @ } T_j = 25^\circ C$$

$$I_D = 89A \text{ @ } T_c = 25^\circ C$$



Application

- Motor control
- Switched Mode Power Supplies
- Uninterruptible Power Supplies

Features

- Power MOS 7[®] MOSFETs
 - Low R_{DSon}
 - Low input and Miller capacitance
 - Low gate charge
 - Avalanche energy rated
 - Very rugged
- Kelvin source for easy drive
- Very low stray inductance
 - Symmetrical design
 - Lead frames for power connections
- Internal thermistor for temperature monitoring
- High level of integration

Benefits

- Outstanding performance at high frequency operation
- Direct mounting to heatsink (isolated package)
- Low junction to case thermal resistance
- Solderable terminals both for power and signal for easy PCB mounting
- Low profile
- RoHS Compliant

Absolute maximum ratings

Symbol	Parameter		Max ratings	Unit
V _{DSS}	Drain - Source Breakdown Voltage		200	V
I _D	Continuous Drain Current	T _c = 25°C	89	A
		T _c = 80°C	66	
I _{DM}	Pulsed Drain current		356	
V _{GS}	Gate - Source Voltage		±30	V
R _{DSon}	Drain - Source ON Resistance		24	mΩ
P _D	Maximum Power Dissipation	T _c = 25°C	357	W
I _{AR}	Avalanche current (repetitive and non repetitive)		89	A
E _{AR}	Repetitive Avalanche Energy		50	mJ
E _{AS}	Single Pulse Avalanche Energy		2500	

CAUTION: These Devices are sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed. See application note APT0502 on www.microsemi.com

All ratings @ $T_j = 25^\circ\text{C}$ unless otherwise specified

Electrical Characteristics

Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit
I_{DSS}	Zero Gate Voltage Drain Current	$V_{GS} = 0V, V_{DS} = 200V$ $T_j = 25^\circ\text{C}$			100	μA
		$V_{GS} = 0V, V_{DS} = 160V$ $T_j = 125^\circ\text{C}$			500	
$R_{DS(on)}$	Drain – Source on Resistance	$V_{GS} = 10V, I_D = 44.5A$		20	24	$\text{m}\Omega$
$V_{GS(th)}$	Gate Threshold Voltage	$V_{GS} = V_{DS}, I_D = 2.5\text{mA}$	3		5	V
I_{GSS}	Gate – Source Leakage Current	$V_{GS} = \pm 30V, V_{DS} = 0V$			± 100	nA

Dynamic Characteristics

Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit
C_{iss}	Input Capacitance	$V_{GS} = 0V$		6850		pF
C_{oss}	Output Capacitance	$V_{DS} = 25V$		2180		
C_{rss}	Reverse Transfer Capacitance	$f = 1\text{MHz}$		97		
Q_g	Total gate Charge	$V_{GS} = 10V$		112		nC
Q_{gs}	Gate – Source Charge	$V_{Bus} = 100V$		43		
Q_{gd}	Gate – Drain Charge	$I_D = 75A$		47		
$T_{d(on)}$	Turn-on Delay Time	Inductive switching @ 125°C $V_{GS} = 15V$ $V_{Bus} = 133V$ $I_D = 75A$ $R_G = 5\Omega$		28		ns
T_r	Rise Time			56		
$T_{d(off)}$	Turn-off Delay Time			81		
T_f	Fall Time			99		
E_{on}	Turn-on Switching Energy	Inductive switching @ 25°C $V_{GS} = 15V, V_{Bus} = 133V$ $I_D = 75A, R_G = 5\Omega$		463		μJ
E_{off}	Turn-off Switching Energy			455		
E_{on}	Turn-on Switching Energy	Inductive switching @ 125°C $V_{GS} = 15V, V_{Bus} = 133V$ $I_D = 75A, R_G = 5\Omega$		608		μJ
E_{off}	Turn-off Switching Energy			531		

Diode ratings and characteristics

Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit
V_{RRM}	Maximum Peak Repetitive Reverse Voltage		200			V
I_{RM}	Maximum Reverse Leakage Current	$V_R = 200V$	$T_j = 25^\circ\text{C}$		250	μA
			$T_j = 125^\circ\text{C}$		500	
I_F	DC Forward Current	$T_c = 85^\circ\text{C}$		30		A
V_F	Diode Forward Voltage	$I_F = 30A$		1.1	1.15	V
		$I_F = 60A$		1.4		
		$I_F = 30A$ $T_j = 125^\circ\text{C}$		0.9		
t_{rr}	Reverse Recovery Time	$I_F = 30A$ $V_R = 133V$ $di/dt = 200A/\mu\text{s}$	$T_j = 25^\circ\text{C}$	24		ns
			$T_j = 125^\circ\text{C}$	48		
Q_{rr}	Reverse Recovery Charge	$I_F = 30A$ $V_R = 133V$ $di/dt = 200A/\mu\text{s}$	$T_j = 25^\circ\text{C}$	33		nC
			$T_j = 125^\circ\text{C}$	150		

Thermal and package characteristics

Symbol	Characteristic		Min	Typ	Max	Unit
R _{thJC}	Junction to Case Thermal Resistance	Transistor			0.35	°C/W
		Diode			1.2	
V _{ISOL}	RMS Isolation Voltage, any terminal to case t = 1 min, I _{isol} < 1mA, 50/60Hz		2500			V
T _J	Operating junction temperature range		-40		150	°C
T _{STG}	Storage Temperature Range		-40		125	
T _C	Operating Case Temperature		-40		100	
Torque	Mounting torque	To Heatsink	M5	2.5	4.7	N.m
Wt	Package Weight				160	g

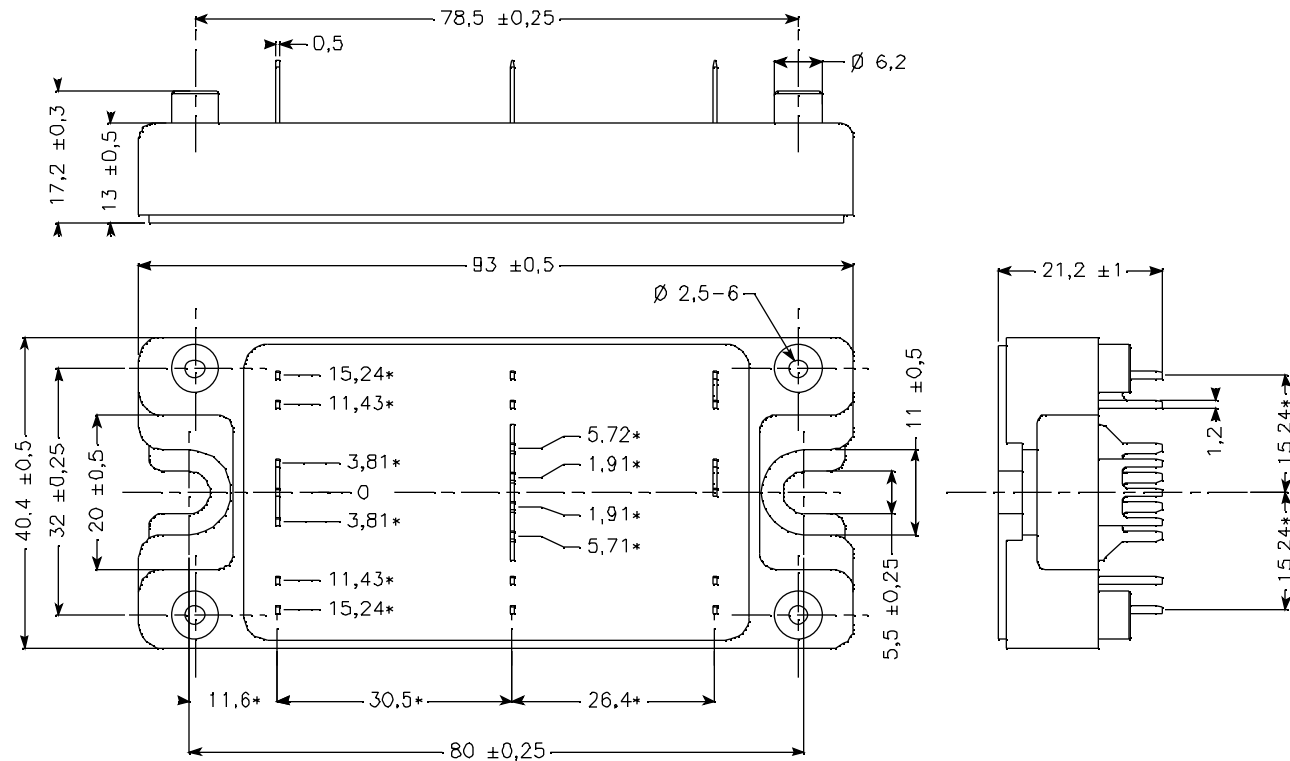
Temperature sensor NTC (see application note APT0406 on www.microsemi.com for more information).

Symbol	Characteristic	Min	Typ	Max	Unit
R ₂₅	Resistance @ 25°C		50		kΩ
B _{25/85}	T ₂₅ = 298.15 K		3952		K

$$R_T = \frac{R_{25}}{\exp \left[B_{25/85} \left(\frac{1}{T_{25}} - \frac{1}{T} \right) \right]}$$

T: Thermistor temperature
R_T: Thermistor value at T

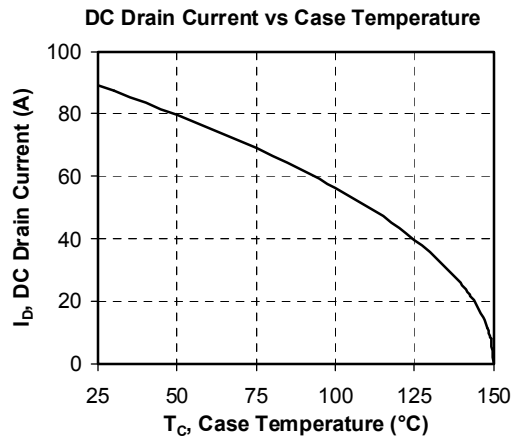
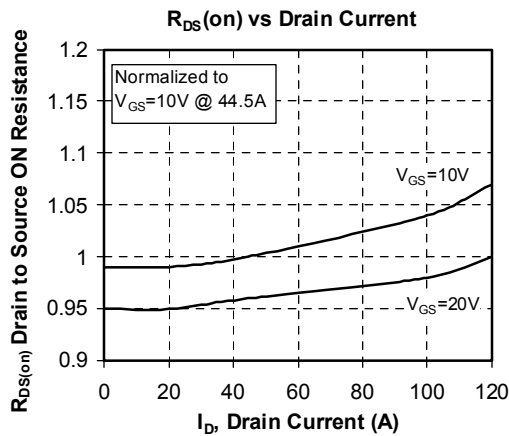
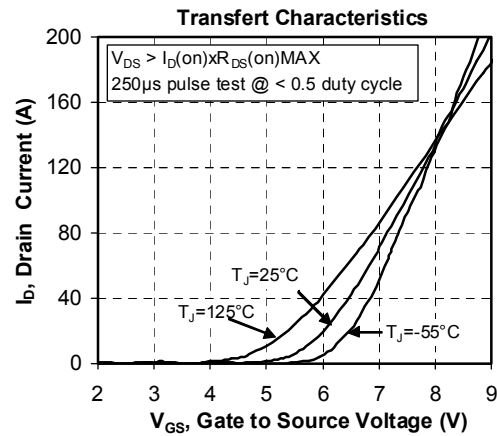
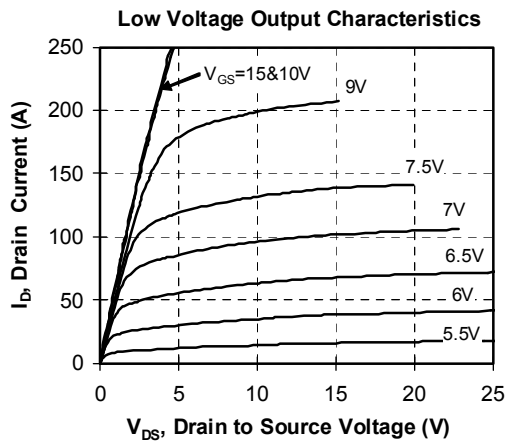
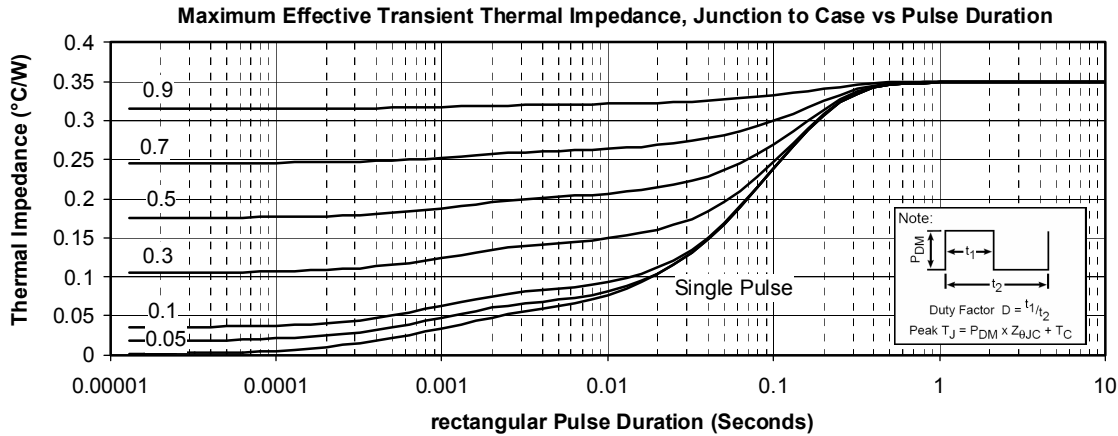
SP4 Package outline (dimensions in mm)

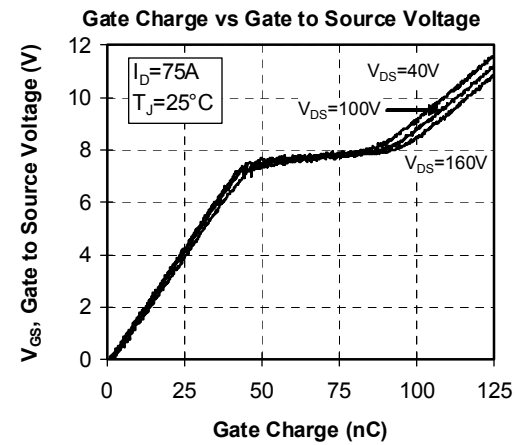
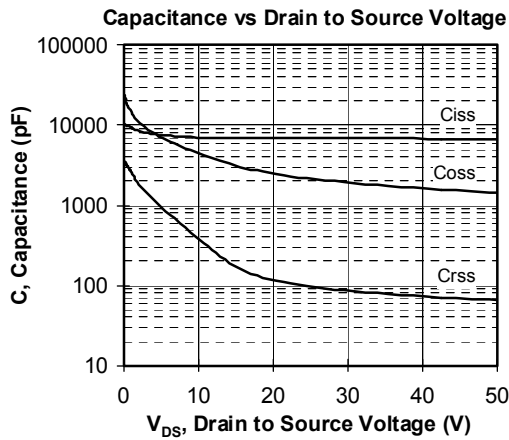
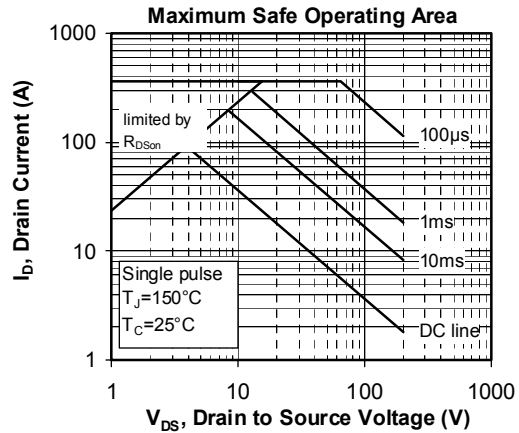
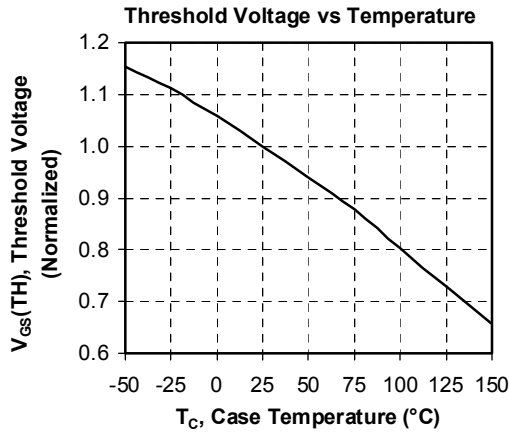
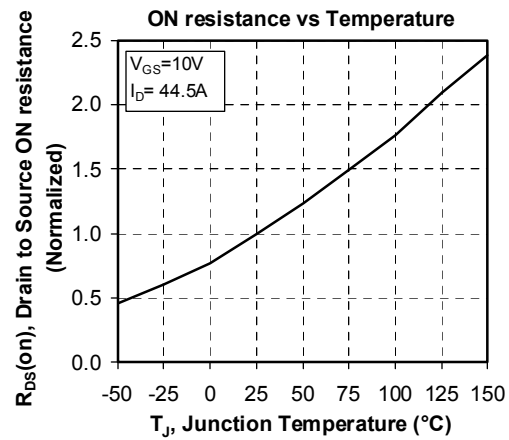
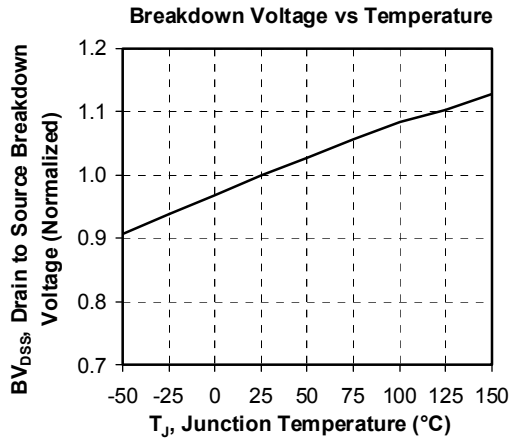


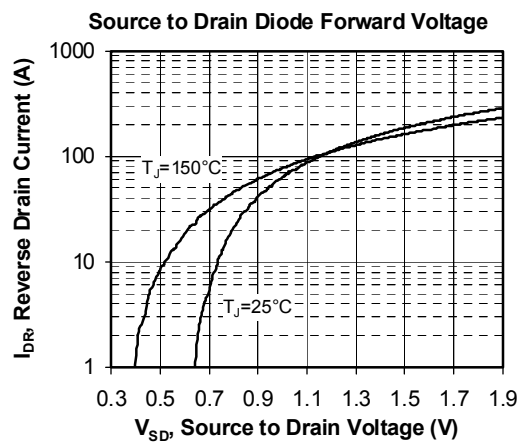
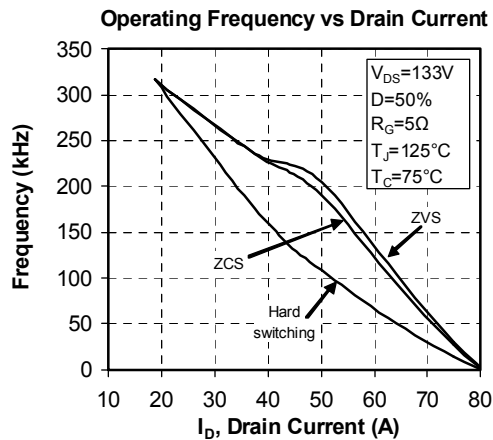
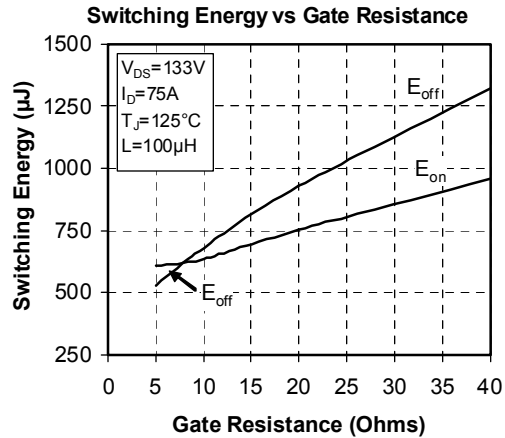
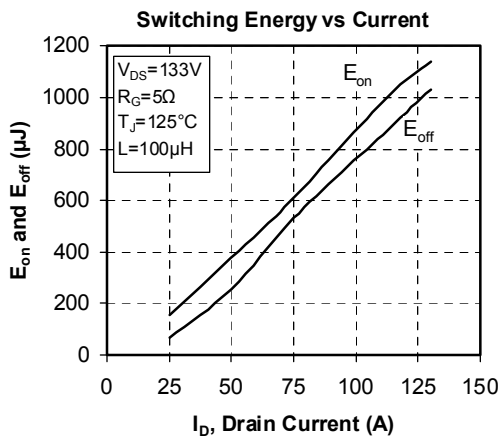
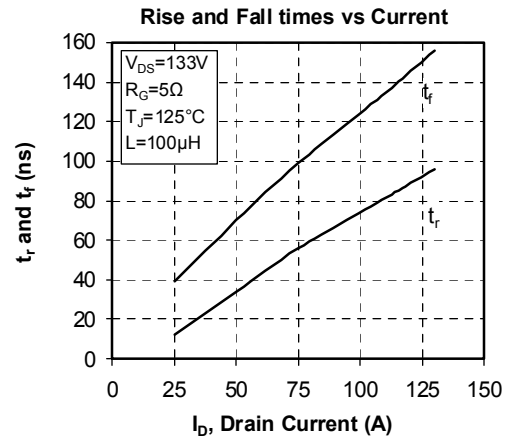
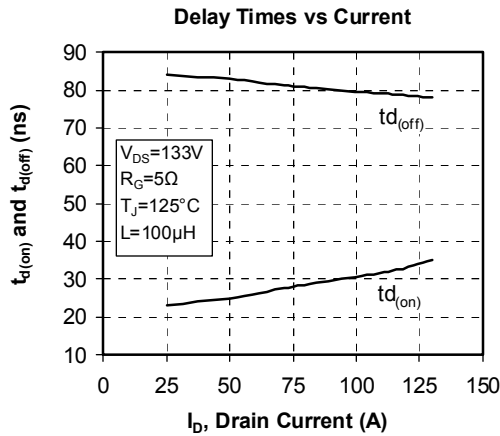
ALL DIMENSIONS MARKED "*" ARE TOLERANCED AS: $\boxed{\oplus \ominus 0.1}$

See application note APT0501 - Mounting Instructions for SP4 Power Modules on www.microsemi.com

Typical Performance Curve







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